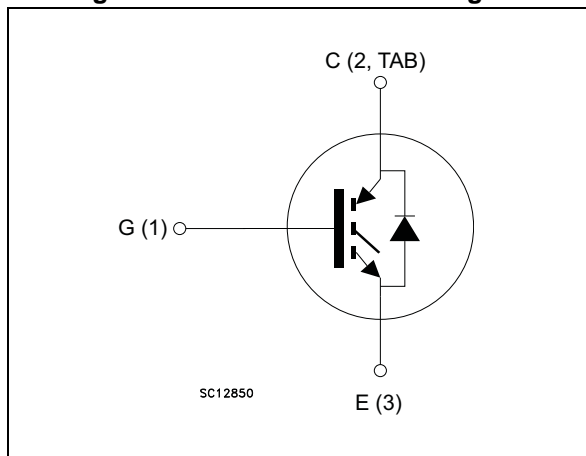


Figure 1. Internal schematic diagram



### Features

- High speed switching
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance
- Short-circuit rated
- Ultrafast soft recovery antiparallel diode

### Applications

- Motor control
- UPS, PFC

### Description

This device is an IGBT developed using an advanced proprietary trench gate and field stop structure. This IGBT series offers the optimum compromise between conduction and switching losses, maximizing the efficiency of very high frequency converters. Furthermore, a positive  $V_{CE(sat)}$  temperature coefficient and very tight parameter distribution result in easier paralleling operation.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STGB20H60DF	GB20H60DF	D <sup>2</sup> PAK	Tape and reel
STGF20H60DF	GF20H60DF	TO-220FP	Tube
STGP20H60DF	GP20H60DF	TO-220	Tube

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	7
<b>3</b>	<b>Test circuits</b> .....	<b>12</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>13</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>19</b>
<b>6</b>	<b>Revision history</b> .....	<b>21</b>



# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	TO-220 D <sup>2</sup> PAK	TO-220FP	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ )	600		V
$I_C$	Continuous collector current at $T_C = 25\text{ °C}$	40	40 <sup>(1)</sup>	A
	Continuous collector current at $T_C = 100\text{ °C}$	20	20 <sup>(1)</sup>	A
$I_{CP}^{(2)}$	Pulsed collector current	80	80 <sup>(1)</sup>	A
$V_{GE}$	Gate-emitter voltage	±20		V
$I_F$	Continuous forward current $T_C = 25\text{ °C}$	40	40 <sup>(1)</sup>	A
	Continuous forward current at $T_C = 100\text{ °C}$	20	20 <sup>(1)</sup>	
$I_{FP}^{(2)}$	Pulsed forward current	80	80 <sup>(1)</sup>	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	167	37	W
$T_{STG}$	Storage temperature range	- 55 to 150		°C
$T_J$	Operating junction temperature	- 55 to 175		

1. Limited by maximum junction temperature.
2. Pulse width limited by maximum junction temperature and turn-off within RBSOA.

**Table 3. Thermal data**

Symbol	Parameter	TO-220 D <sup>2</sup> PAK	TO-220FP	Unit
$R_{thJC}$	Thermal resistance junction-case IGBT	0.9	4	°C/W
$R_{thJC}$	Thermal resistance junction-case diode	2.5	5.6	°C/W
$R_{thJA}$	Thermal resistance junction-ambient	62.5		°C/W

## 2 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified.

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ( $V_{GE} = 0$ )	$I_C = 2\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 20\text{ A}$		1.6	2.0	V
		$V_{GE} = 15\text{ V}, I_C = 20\text{ A}$ $T_J = 125\text{ °C}$		1.75		
		$V_{GE} = 15\text{ V}, I_C = 20\text{ A}$ $T_J = 175\text{ °C}$		1.8		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	5.0	6.0	7.0	V
$I_{CES}$	Collector cut-off current ( $V_{GE} = 0$ )	$V_{CE} = 600\text{ V}$			25	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current ( $V_{CE} = 0$ )	$V_{GE} = \pm 20\text{ V}$			250	nA

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GE} = 0$	-	2750	-	pF
$C_{oes}$	Output capacitance		-	110	-	pF
$C_{res}$	Reverse transfer capacitance		-	65	-	pF
$Q_g$	Total gate charge	$V_{CC} = 400\text{ V}, I_C = 20\text{ A},$ $V_{GE} = 15\text{ V}$	-	115	-	nC
$Q_{ge}$	Gate-emitter charge		-	22	-	nC
$Q_{gc}$	Gate-collector charge		-	45	-	nC

Table 6. Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 20\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$		42.5	-	ns
$t_r$	Current rise time			11.9	-	ns
$(di/dt)_{on}$	Turn-on current slope			1345	-	A/ $\mu$ s
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 20\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ $T_J = 175\text{ }^\circ\text{C}$		42.5	-	ns
$t_r$	Current rise time			13.4		ns
$(di/dt)_{on}$	Turn-on current slope			1180		A/ $\mu$ s
$t_{r(Voff)}$	Off voltage rise time	$V_{CE} = 400\text{ V}$ , $I_C = 20\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$		20	-	ns
$t_{d(off)}$	Turn-off delay time			177	-	ns
$t_f$	Current fall time			55	-	ns
$t_{r(Voff)}$	Off voltage rise time	$V_{CE} = 400\text{ V}$ , $I_C = 20\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ $T_J = 175\text{ }^\circ\text{C}$		26	-	ns
$t_{d(off)}$	Turn-off delay time			173	-	ns
$t_f$	Current fall time			86	-	ns
$t_{sc}$	Short-circuit withstand time	$V_{CC} \leq 360\text{ V}$ , $V_{GE} = 15\text{ V}$	3	5	-	$\mu$ s

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CE} = 400\text{ V}$ , $I_C = 20\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$	-	209	-	$\mu$ J	
$E_{off}^{(2)}$	Turn-off switching losses			-	261	-	$\mu$ J
$E_{ts}$	Total switching losses			-	470	-	$\mu$ J
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CE} = 400\text{ V}$ , $I_C = 20\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ $T_J = 175\text{ }^\circ\text{C}$	-	480	-	$\mu$ J	
$E_{off}^{(2)}$	Turn-off switching losses			-	416	-	$\mu$ J
$E_{ts}$	Total switching losses			-	896	-	$\mu$ J

1. Energy losses include reverse recovery of the diode.
2. Turn-off losses include also the tail of the collector current.

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward on-voltage	$I_F = 20\text{ A}$ $I_F = 20\text{ A}, T_J = 175\text{ °C}$	-	1.8	2.2	V
				1.3		V
$t_{rr}$	Reverse recovery time	$V_r = 60\text{ V}; I_F = 20\text{ A};$ $di_F/dt = 100\text{ A} / \mu\text{s}$	-	90	-	ns
$Q_{rr}$	Reverse recovery charge			110		nC
$I_{rrm}$	Reverse recovery current			2.4		A
$t_{rr}$	Reverse recovery time	$V_r = 60\text{ V}; I_F = 20\text{ A};$ $di_F/dt = 100\text{ A} / \mu\text{s}$ $T_J = 175\text{ °C}$	-	180	-	ns
				466		nC
$I_{rrm}$	Reverse recovery current		-	5.2	-	A

## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics ( $T_J = 25^\circ\text{C}$ )

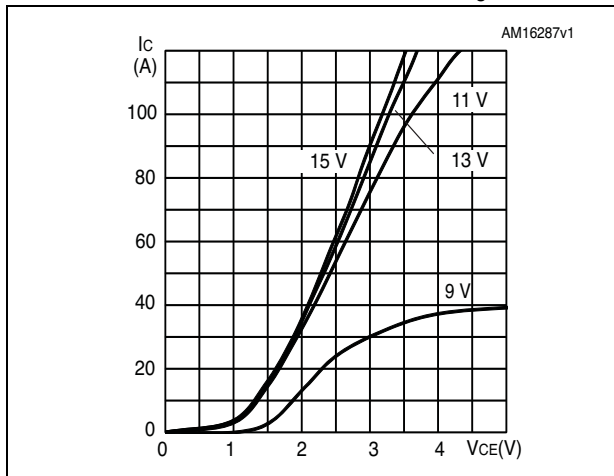


Figure 3. Output characteristics ( $T_J = 175^\circ\text{C}$ )

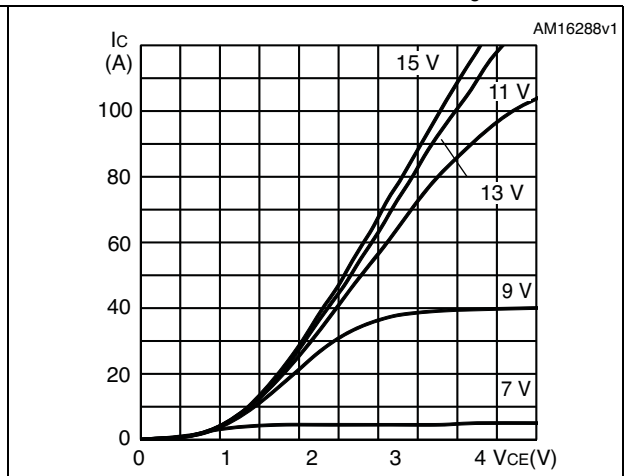


Figure 4. Transfer characteristics

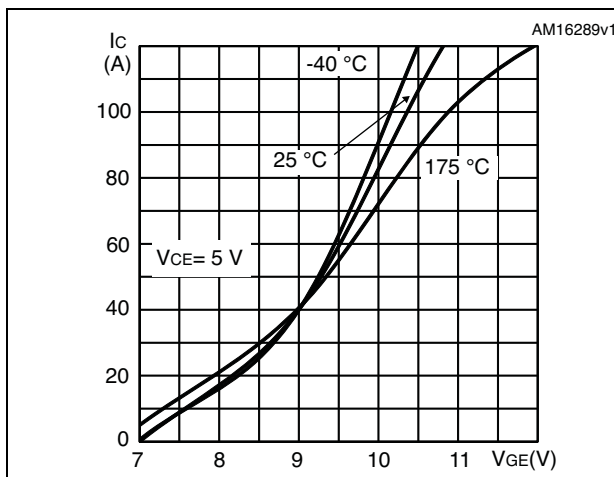


Figure 5. Normalized  $V_{GE(th)}$  vs junction temperature

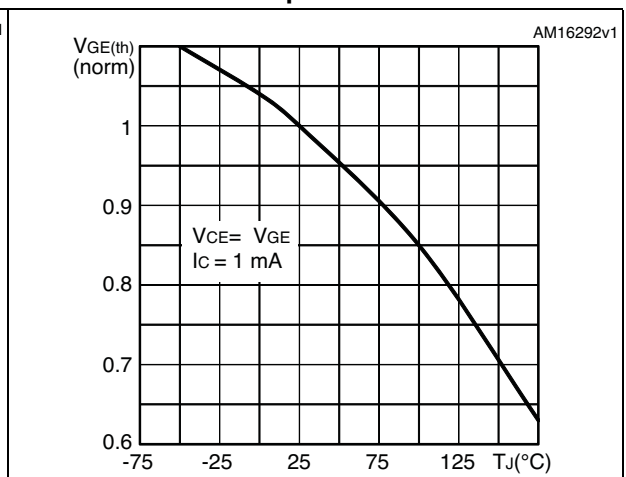


Figure 6. Collector current vs. case temperature for D<sup>2</sup>PAK and TO-220 Figure 7. Collector current vs. case temperature for TO-220FP

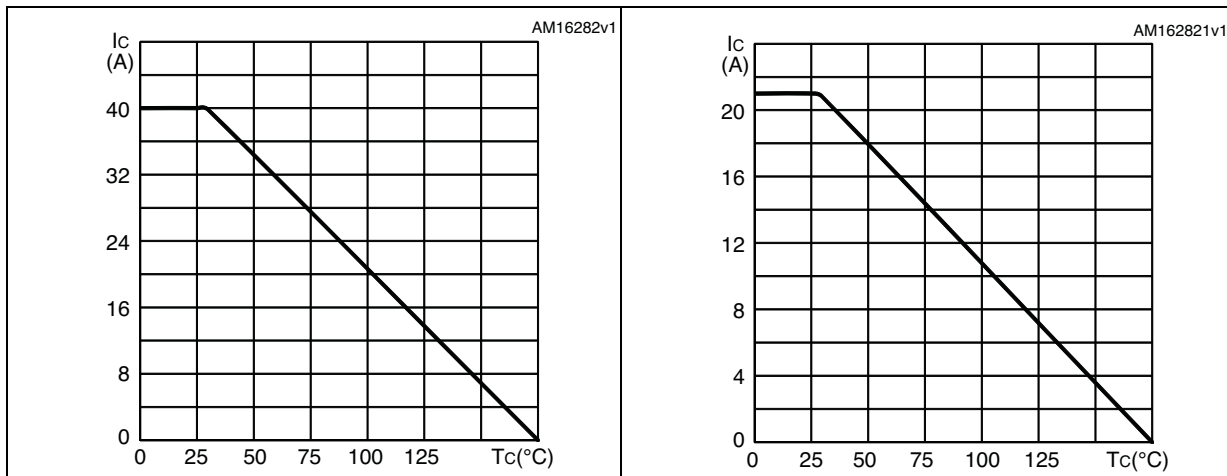


Figure 8. Collector current vs. frequency for D<sup>2</sup>PAK and TO-220

Figure 9. Collector current vs. frequency for TO-220FP

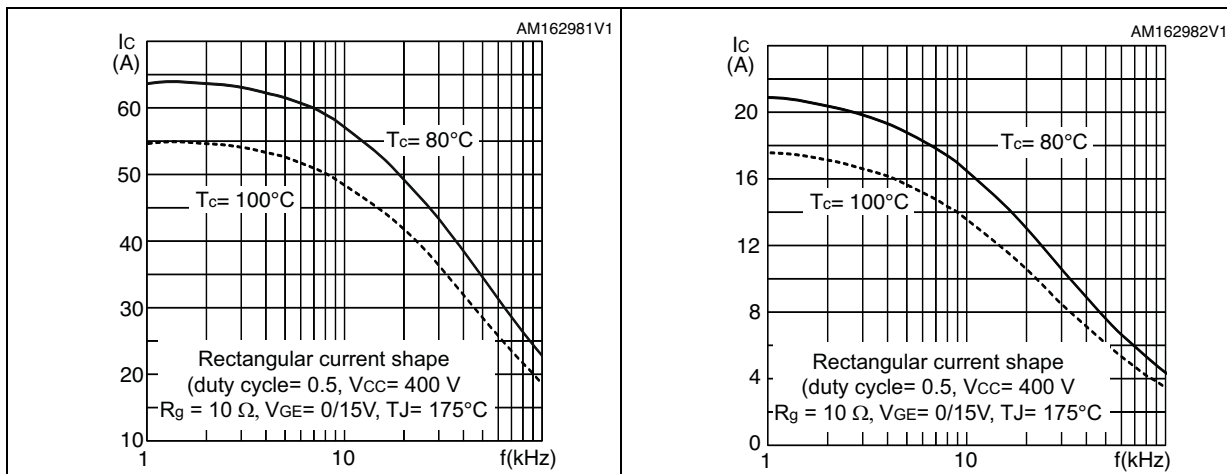


Figure 10. Power dissipation vs. case temperature for D<sup>2</sup>PAK and TO-220

Figure 11. Power dissipation vs. case temperature for TO-220FP

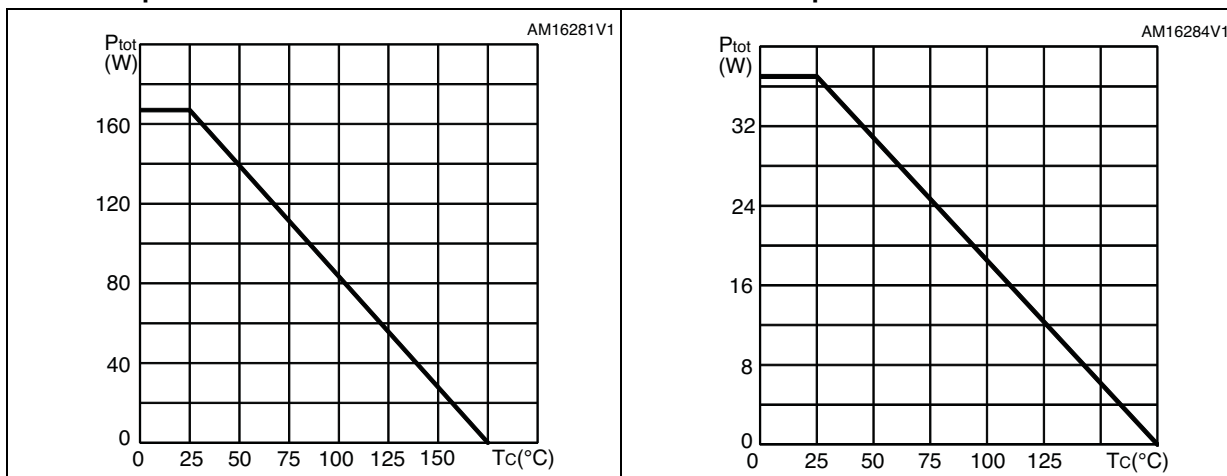




Figure 12.  $V_{CE(sat)}$  vs. junction temperature

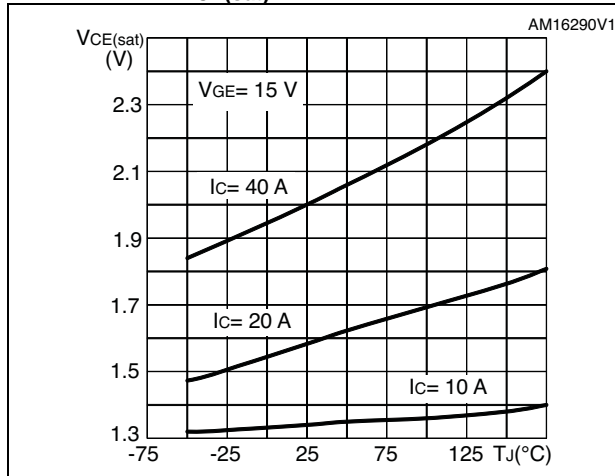


Figure 13.  $V_{CE(sat)}$  vs. collector current

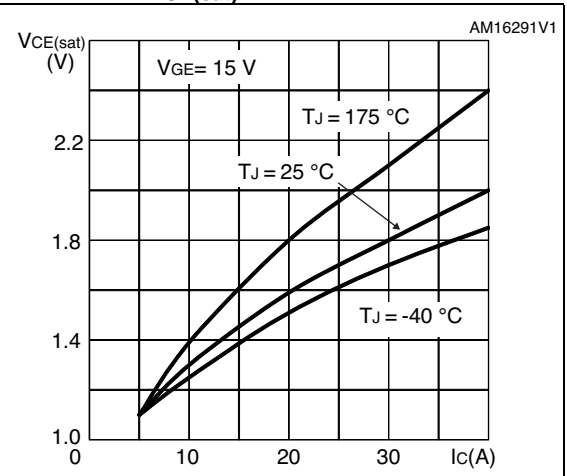


Figure 14. Forward bias safe operating area for D<sup>2</sup>PAK and TO-220

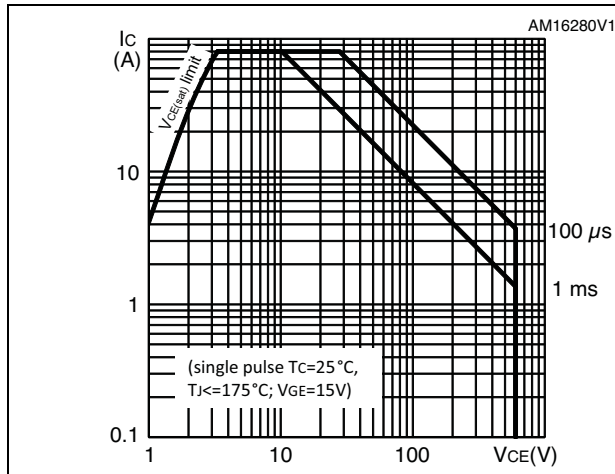


Figure 15. Thermal impedance for D<sup>2</sup>PAK and TO-220

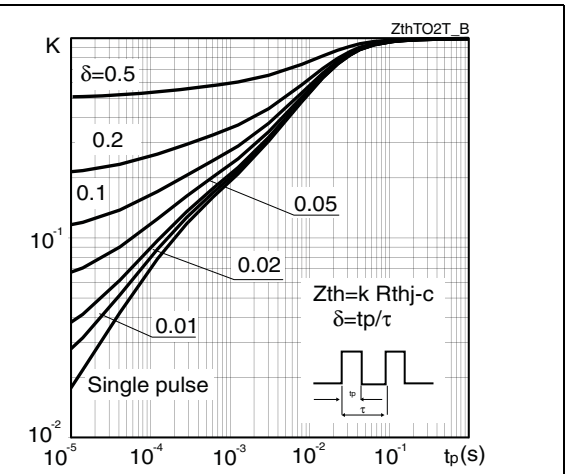


Figure 16. Forward bias safe operating area for TO-220FP

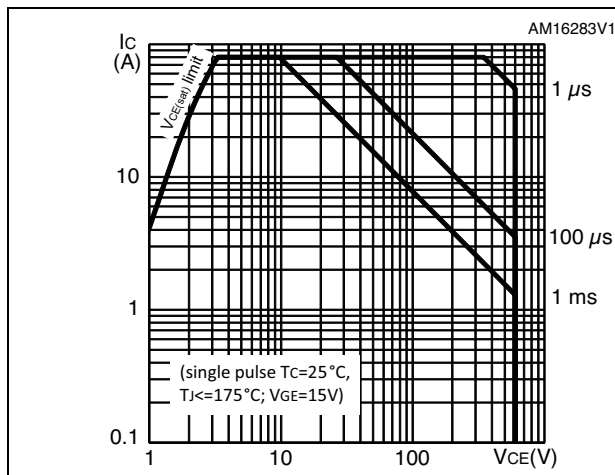


Figure 17. Thermal impedance for TO-220FP

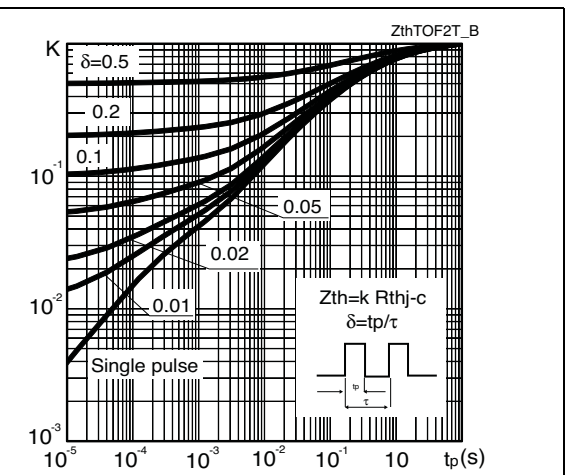


Figure 18. Diode  $V_F$  vs. forward current

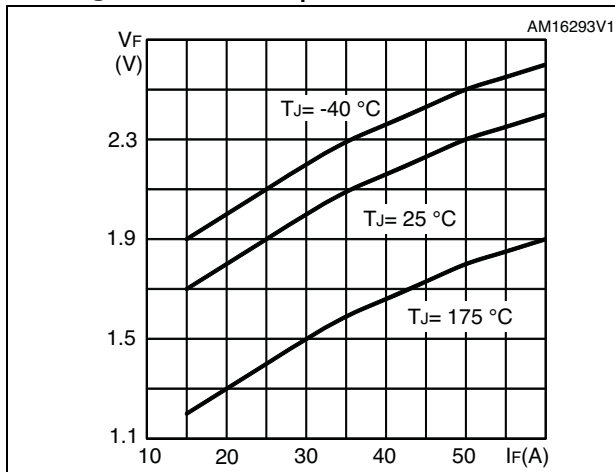


Figure 19. Gate charge vs. gate-emitter voltage

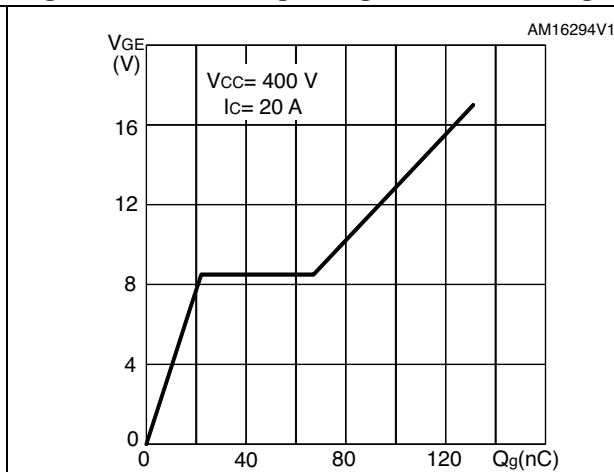


Figure 20. Capacitance variations vs.  $V_{CE}$

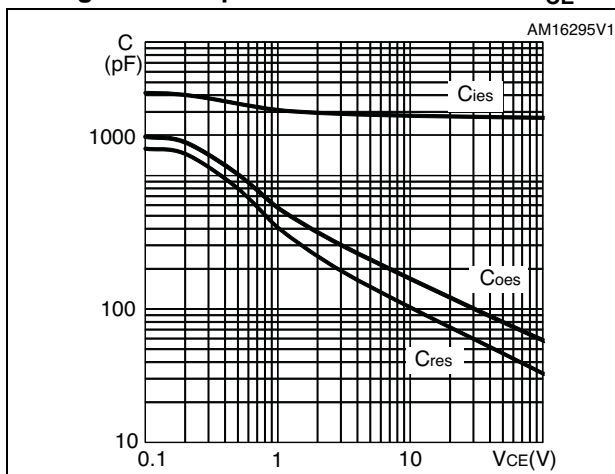


Figure 21. Switching losses vs. gate resistance

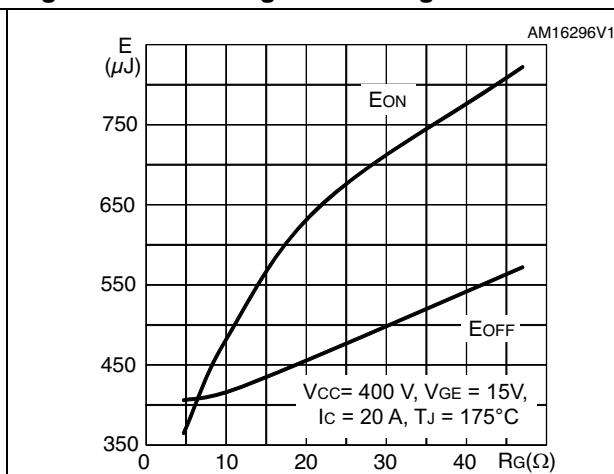


Figure 22. Switching losses vs. collector current

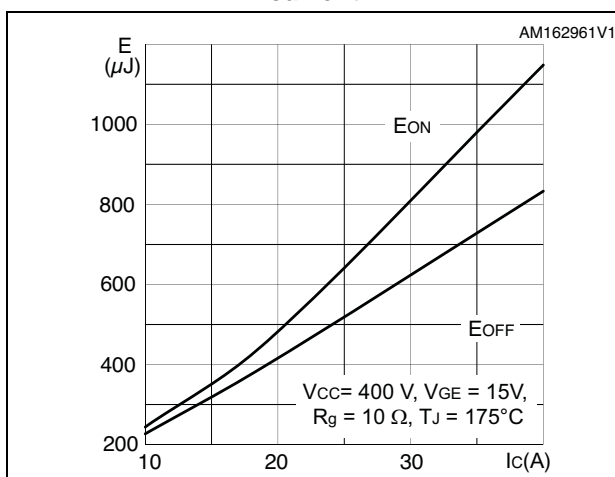


Figure 23. Switching losses vs. temperature

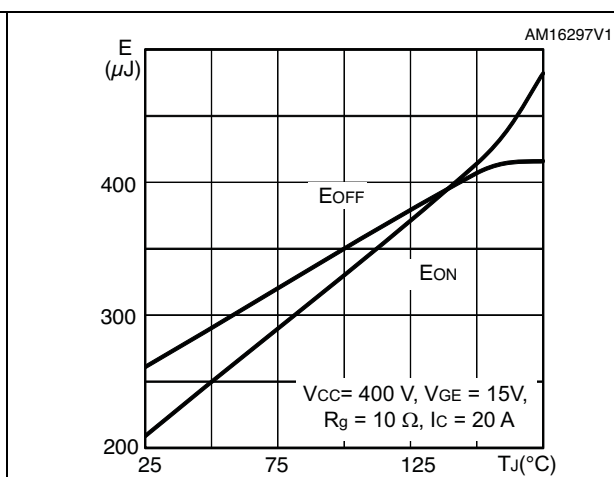
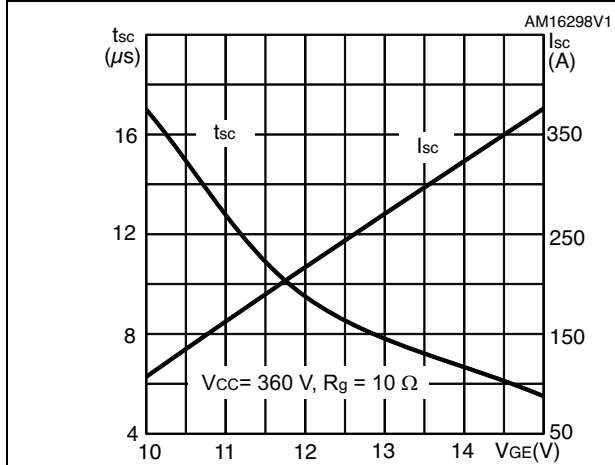


Figure 24. Short-circuit time and current vs.  $V_{GE}$



### 3 Test circuits

Figure 25. Test circuit for inductive load switching



Figure 26. Gate charge test circuit

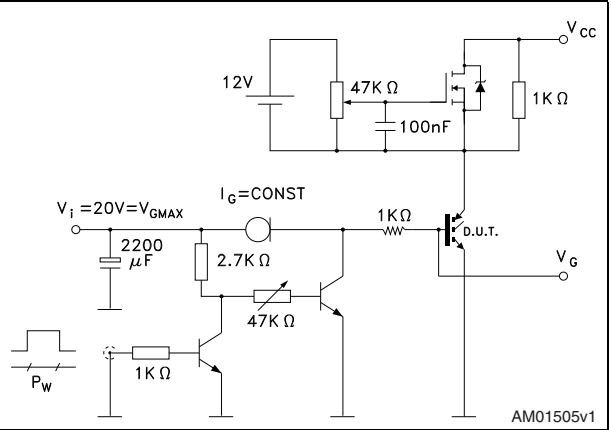


Figure 27. Switching waveform

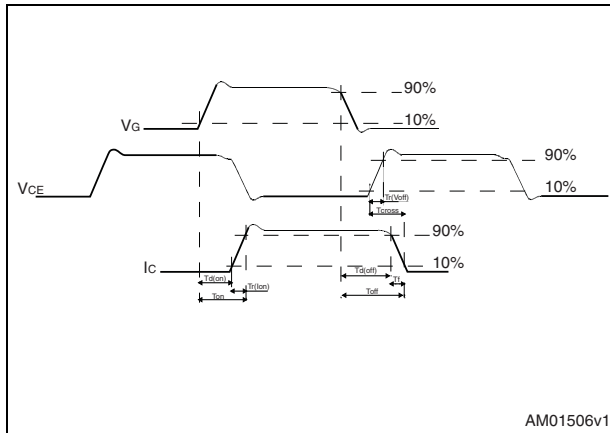
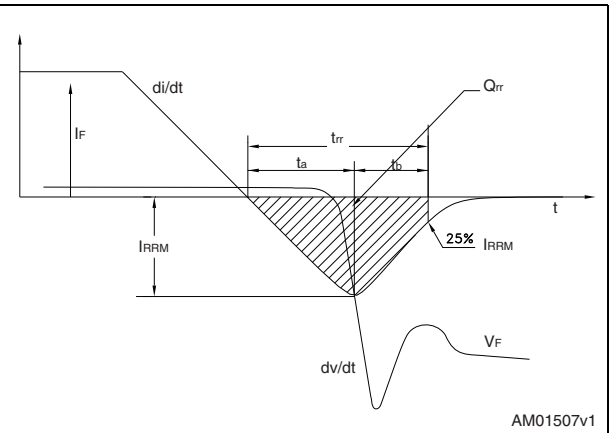


Figure 28. Diode recovery time waveform



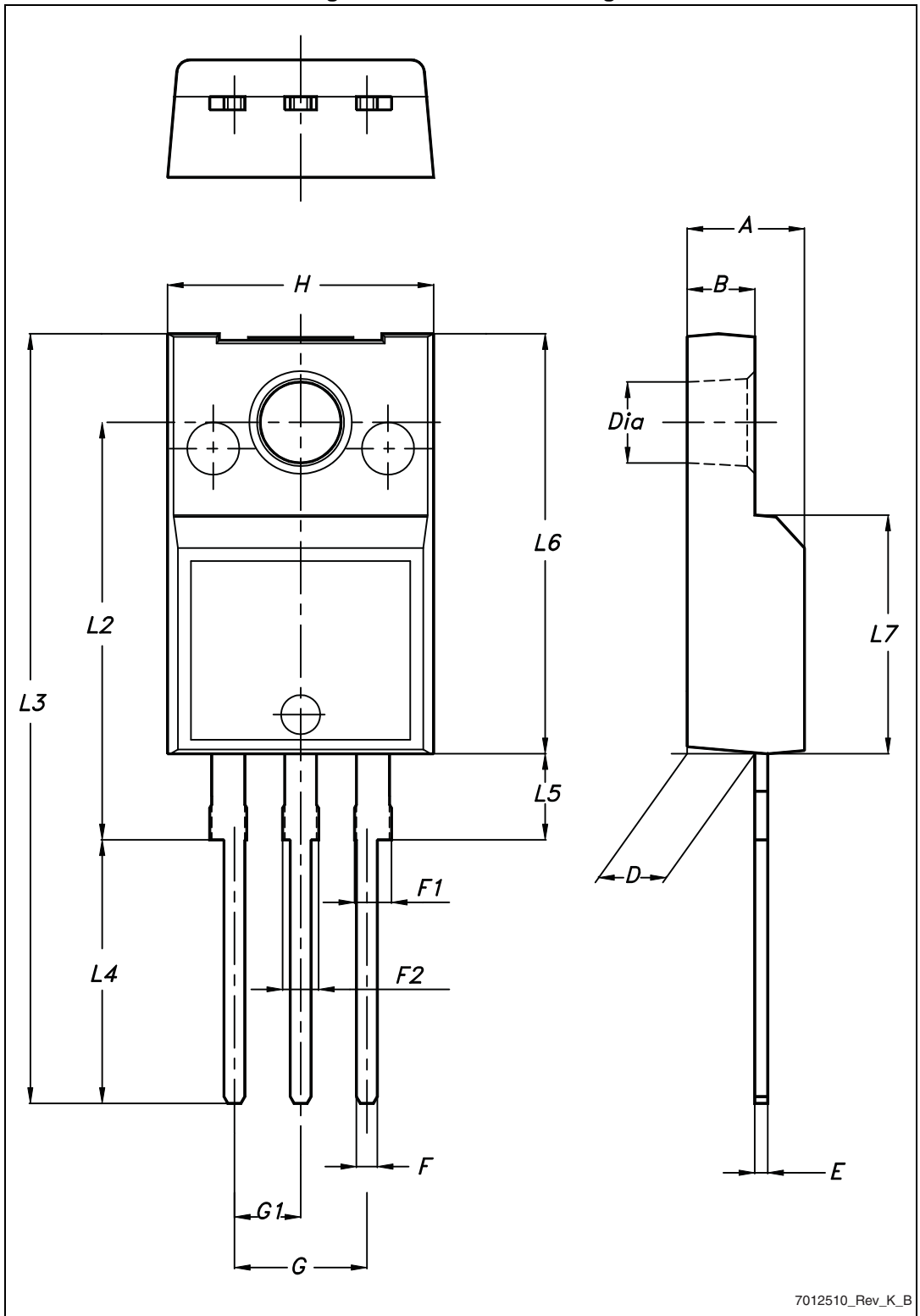
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 9. TO-220FP mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 29. TO-220FP drawing



7012510\_Rev\_K\_B

Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 30. TO-220 type A drawing

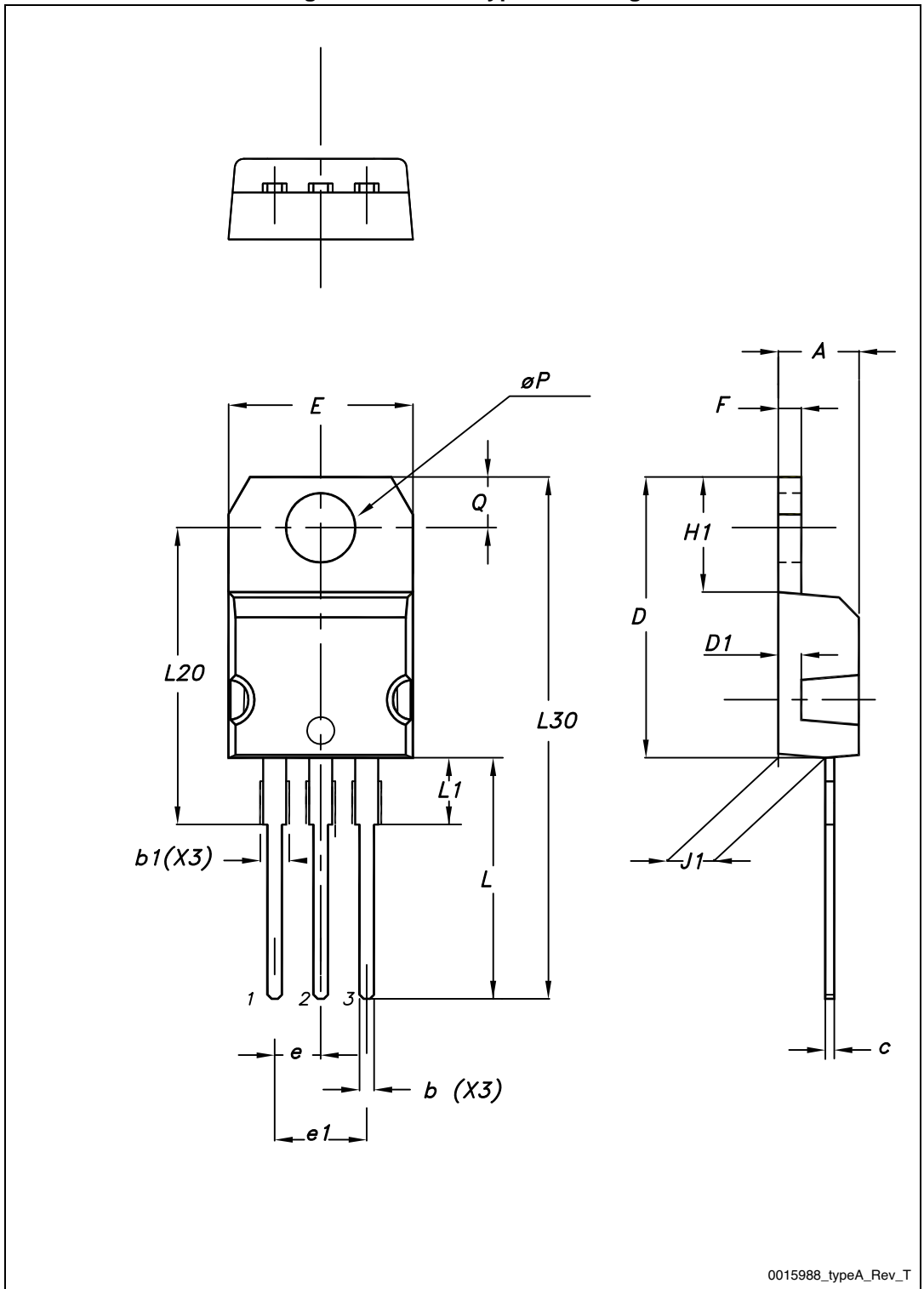




Table 11. D<sup>2</sup>PAK mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 31. D<sup>2</sup>PAK drawing

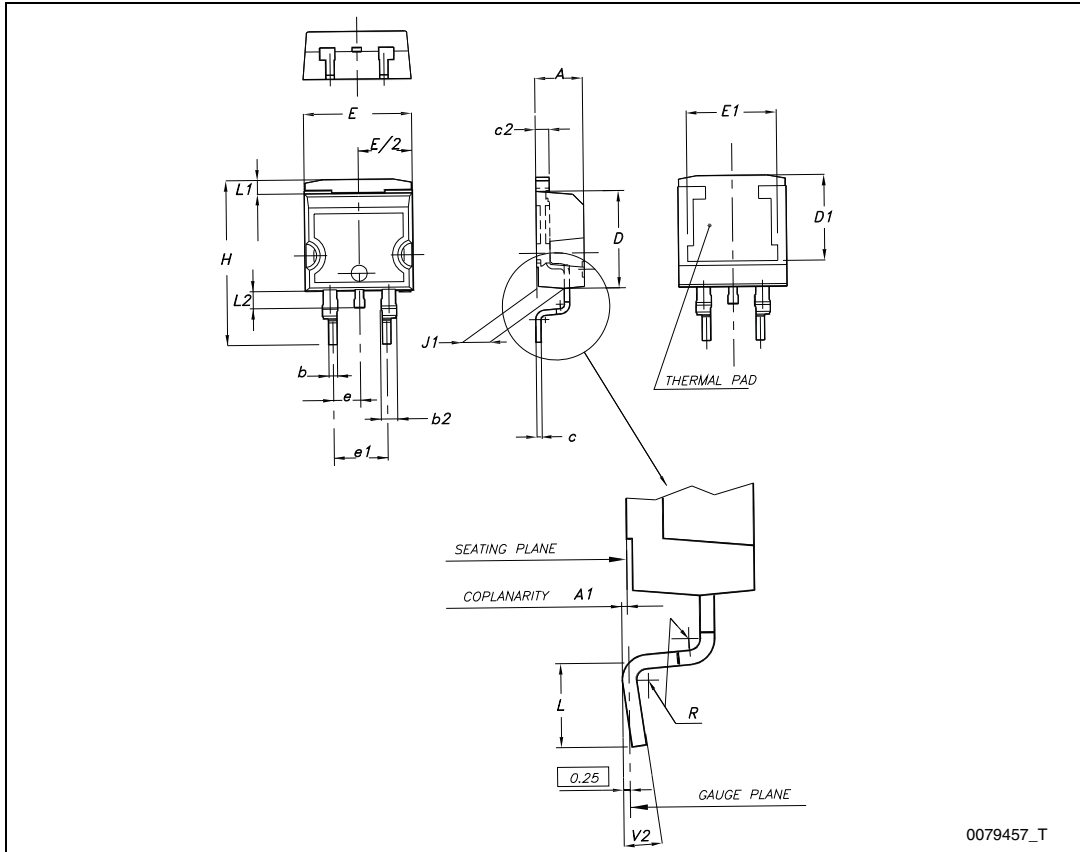
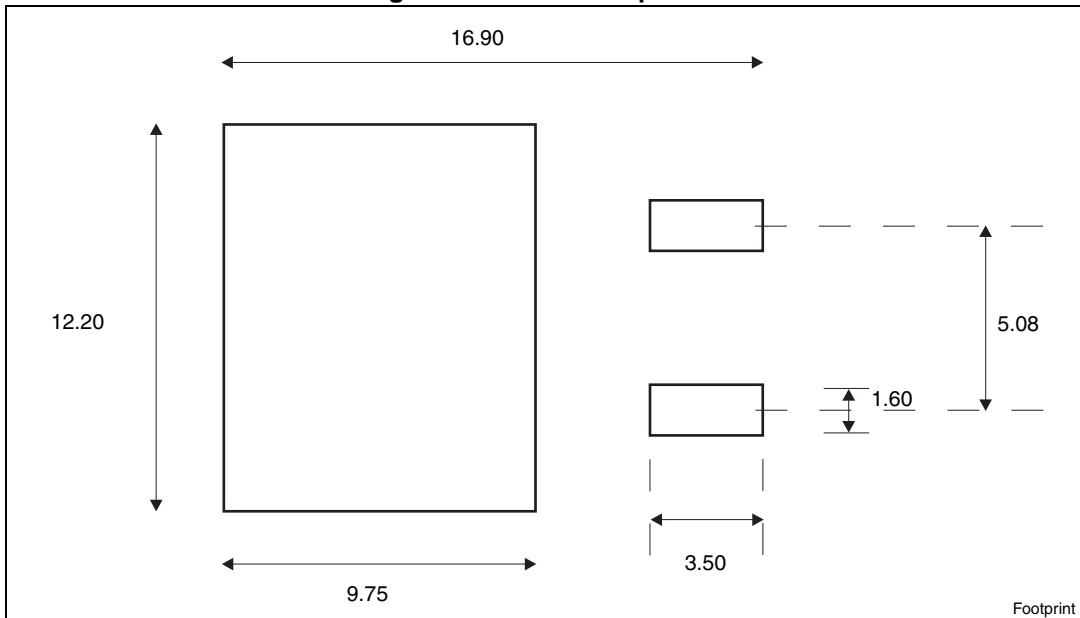


Figure 32. D<sup>2</sup>PAK footprint<sup>(a)</sup>



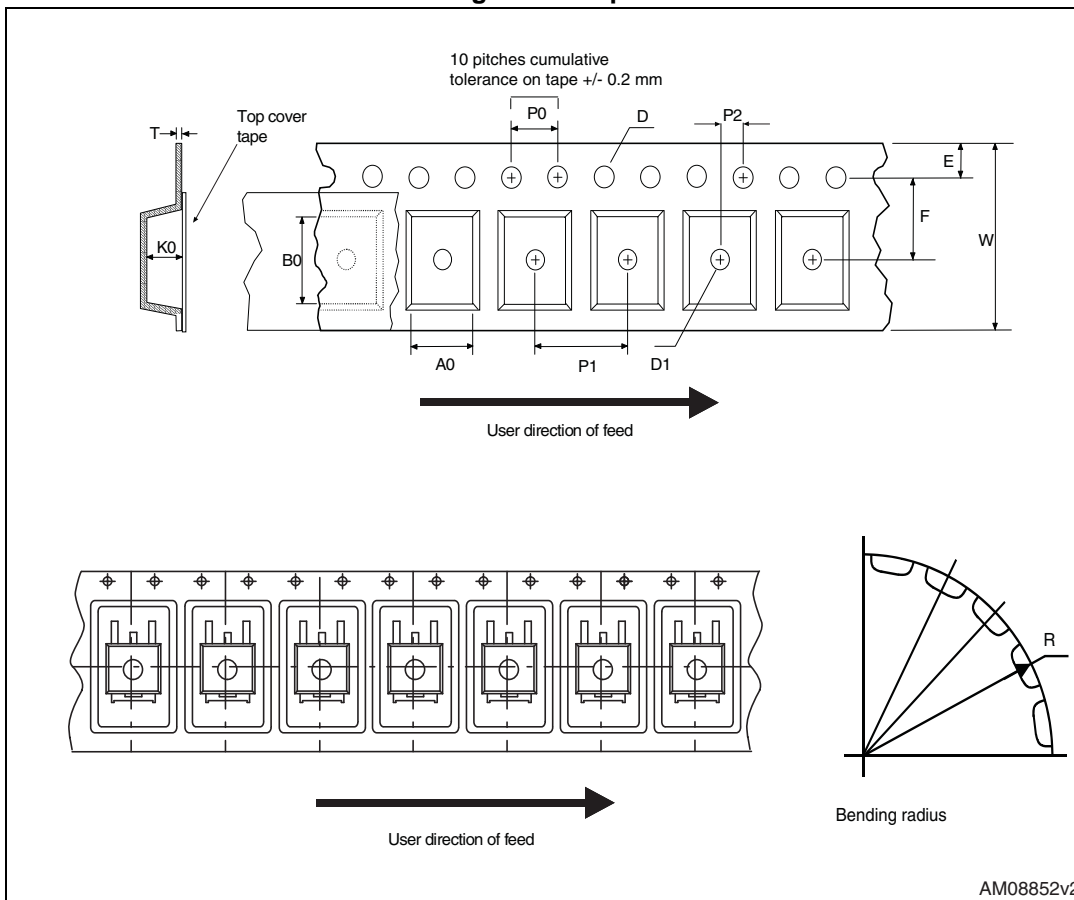
a. All dimension are in millimeters

## 5 Packaging mechanical data

Table 12. D<sup>2</sup>PAK tape and reel mechanical data

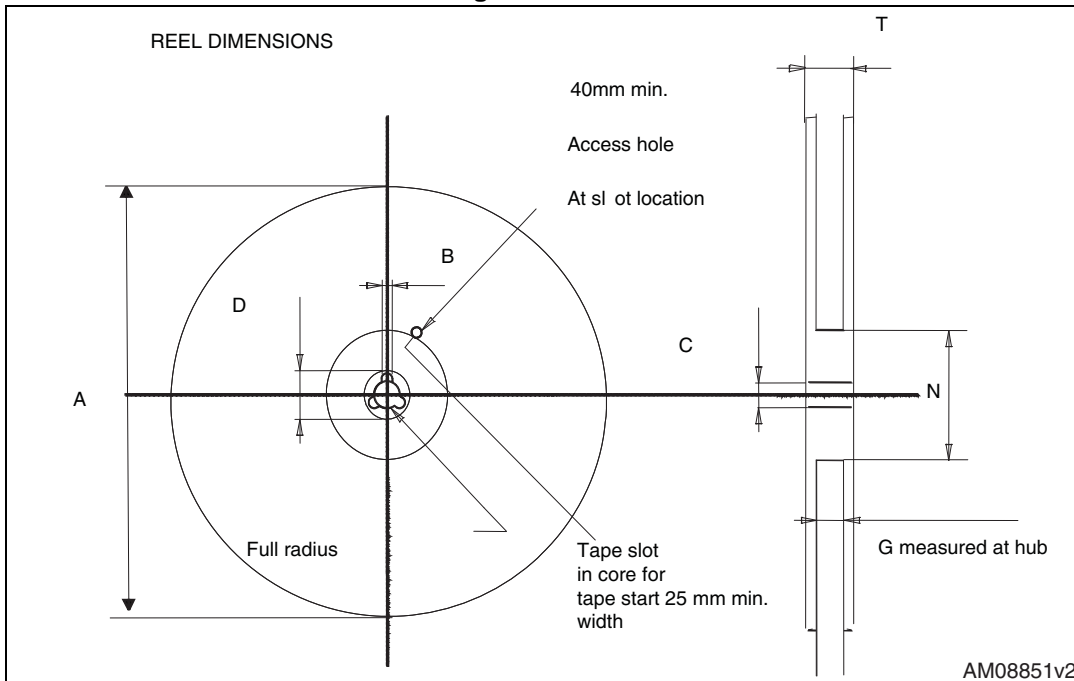
Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 33. Tape



AM08852v2

Figure 34. Reel



AM08851v2

## 6 Revision history

Table 13. Document revision history

Date	Revision	Changes
03-Oct-2012	1	Initial release.
18-Mar-2013	2	Added new order code STGF20H60DF, mechanical data <a href="#">Table 9</a> and <a href="#">Figure 29 on page 14</a> . Added <a href="#">Chapter 2.1: Electrical characteristics (curves)</a> .
22-Mar-2013	3	Document status promoted from preliminary to production data.
03-Jun-2013	4	Updated $P_{TOT}$ in <a href="#">Table 2: Absolute maximum ratings</a> , $R_{thJC}$ in <a href="#">Table 3: Thermal data</a> and <a href="#">Figure 10: Power dissipation vs. case temperature for D<sup>2</sup>PAK and TO-220</a> . Updated <a href="#">Section 4: Package mechanical data</a> for TO-220.

**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**ST PRODUCTS ARE NOT AUTHORIZED FOR USE IN WEAPONS. NOR ARE ST PRODUCTS DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2013 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[STMicroelectronics:](#)

[STGF20H60DF](#) [STGP20H60DF](#) [STGB20H60DF](#)